

# ESDALC6V1P5

## QUAD LOW CAPACITANCE TRANSIL™ **Application Specific Discretes** ARRAY FOR ESD PROTECTION

MAIN APPLICATIONS

Where transient overvoltage protection in ESD sensitive equipment is required, such as :

A.S.D.

- Computers
- Printers
- Communication systems and cellular phones
- Video equipment

This device is particularly adapted to the protection of symmetrical signals.

## **FEATURES**

- 4 UNIDIRECTIONAL TRANSIL<sup>™</sup> FUNCTIONS.
- BREAKDOWN VOLTAGE V<sub>BR</sub> = 6.1V MIN.
- LOW DIODE CAPACITANCE (12pF @ 0V)
- LOW LEAKAGE CURRENT < 100 nA</p>
- VERY SMALL PCB AREA < 2.6 mm<sup>2</sup>

## DESCRIPTION

The ESDALC6V1P5 is a monolithic array designed to protect up to 4 lines against ESD transients.

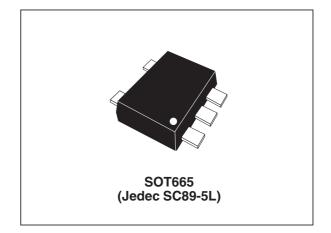
This device is ideal for applications where both reduced line capacitance and board space saving are required.

## BENEFITS

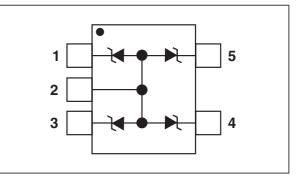
- High ESD protection level.
- High integration.
- Suitable for high density boards.

#### **COMPLIES WITH THE FOLLOWING STANDARDS:**

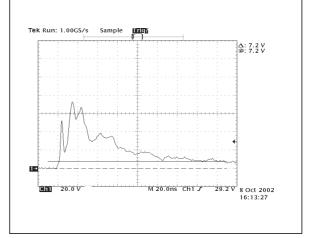
- IEC61000-4-2 level 4: 15 kV (air discharge) 8 kV (contact discharge)
- MIL STD 883E-Method 3015-7: class 3 25kV HBM (Human Body Model)



#### **FUNCTIONAL DIAGRAM**



#### ESD response to IEC61000-4-2 level 4 (15kV contact)



#### February 2004 - Ed: 1

# ESDALC6V1P5

# **ABSOLUTE RATINGS** ( $T_{amb} = 25^{\circ}C$ )

Symbol	Parameter	Test conditions	Value	Unit
V <sub>PP</sub>	ESD discharge - IEC61000-4 IEC61000-4	± 15 ± 8	kV	
P <sub>PP</sub>	Peak pulse power (8/20 µs) (	30	W	
Tj	Junction temperature	125	°C	
T <sub>stg</sub>	Storage temperature range	- 55 to + 150	°C	
TL	Maximum lead temperature fo	260	°C	
T <sub>op</sub>	Operating temperature range	- 40 to + 125	°C	

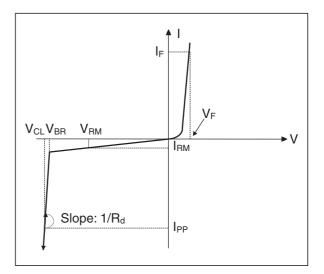
Note 1: for a surge greater than the maximum values, the diode will fail in short-circuit.

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-a)</sub>	Junction to ambient on printed circuit on recommended pad layout	220	°C/W

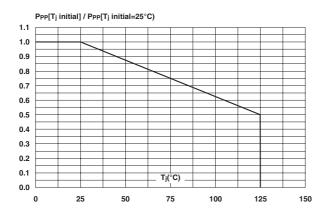
# ELECTRICAL CHARACTERISTICS (T<sub>amb</sub> = 25°C)

Symbol	Parameter
V <sub>RM</sub>	Stand-off voltage
V <sub>BR</sub>	Breakdown voltage
V <sub>CL</sub>	Clamping voltage
I <sub>RM</sub>	Leakage current
I <sub>PP</sub>	Peak pulse current
αΤ	Voltage tempature coefficient
VF	Forward voltage drop
С	Capacitance per line
R <sub>d</sub>	Dynamic resistance



	V	BR @	I <sub>R</sub>	I <sub>RM</sub> @	V <sub>RM</sub>	Rd	αΤ	С
Types	min.	max.		max.		typ.	max.	typ.
Types								@ 0V
	V	V	mA	μA	V	Ω	10 <sup>-4</sup> /°C	pF
ESDALC6V1P5	6.1	7.2	1	0.1	3	1.5	4.5	12

# **Fig. 1:** Relative variation of peak pulse power versus initial junction temperature.



**Fig. 2:** Peak pulse power versus exponential pulse duration.

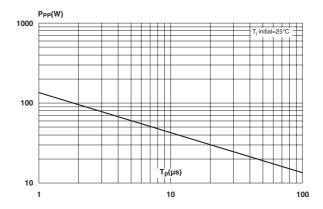


Fig. 3: Clamping voltage versus peak pulse current (typical values, rectangular waveform).

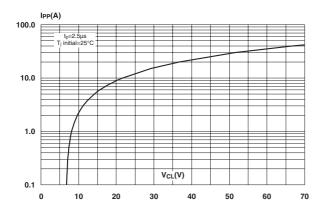
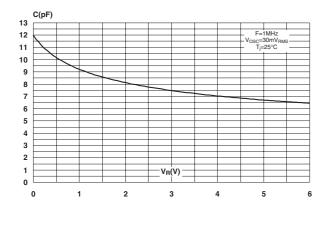
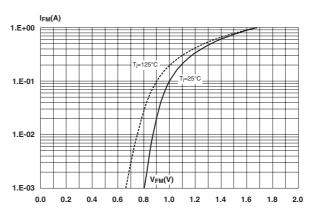


Fig. 5: Junction capacitance versus reverse voltage applied (typical values).

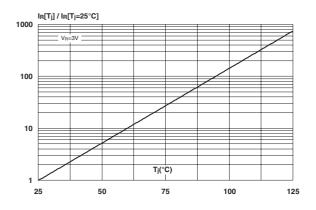


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**Fig. 4:** Forward voltage drop versus peak forward current (typical values).

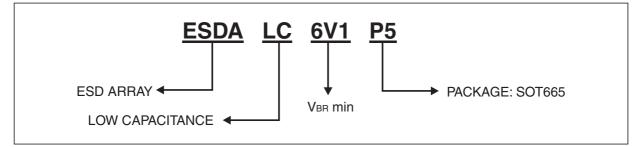


**Fig. 6:** Relative variation of leakage current versus junction temperature (typical values).



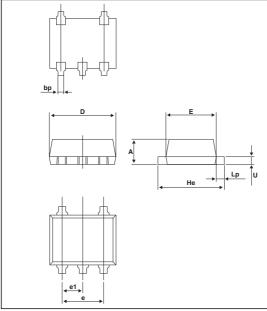
## ESDALC6V1P5

## ORDER CODE



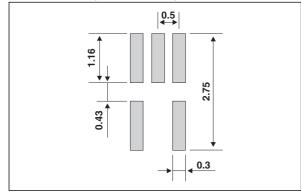
Ordering type	Marking	Package	Weight	Base qty	Delivery mode
ESDALC6V1P5	A1	SOT665	2.9 mg.	3000	Tape & reel

## PACKAGE MECHANICAL DATA SOT-665

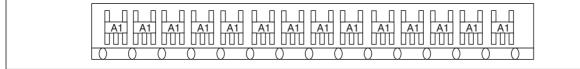


	DIMENSIONS					
REF.	Millim	neters	Inches			
	Min.	Max.	Min.	Max.		
А	0.50	0.60	0.020	0.024		
bp	0.17	0.27	0.007	0.011		
С	0.08	0.18	0.003	0.007		
D	1.50	1.70	0.060	0.067		
Е	1.10	1.30	0.043	0.051		
е	1.00		0.040			
e1	0.50		0.020			
He	1.50	1.70	0.059	0.067		
Lp	0.10	0.30	0.004	0.012		

FOOT PRINT (in millimeters)



## **REEL ORIENTATION**



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